

## Schottky Barrier Diode

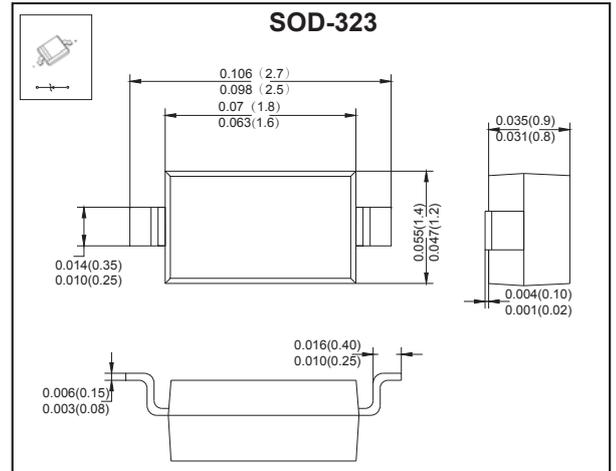
VOLTAGE RANGE: 30V PEAK PULSE POWER:250mW

### FEATURES

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge
- Ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications

### MECHANICAL DATA

- Case: SOD-323 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



## MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 C ambient temperature unless otherwise specified

Parameter	Symbol	Limit	Unit
Non-repetitive peak reverse voltage	VRM	30	V
Forward current	IFM	200	mA
Non-repetitive Forward Surge Current @t=8.3ms	IFSM	1	A
Power dissipation	Ptot	250	mW
Thermal resistance junction to ambient	ReJA	400	°C/W
Junction temperature	TJ	125	°C
Storage temperature	TSTG	-55~+150	°C

Electrical Specification (TA=25@25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	VR	30			V	IR=100uA
Forward voltage	VF		260 320 420 490	550	mV	IF=2mA IF=15mA IF=100mA IF=200mA
Reverse current	IR			5	μA	VR=30V
Capacitance between terminals	CT			15	pF	VR=10V,f=1MHz

MARKING: S21

# RATINGS AND CHARACTERISTIC CURVES

## Typical Characteristics

